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Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V _{DS} (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.00233			
I _D (A)	100			
Configuration	Single			
Package	TO-252			

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



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N-Channel MOSFET	o _s

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	40		
Gate-source voltage		V_{GS}	± 20	V	
Continuous drain current	T _C = 25 °C ^a	I _D	100		
	T _C = 125 °C		87.5		
Continuous source current (diode conduction)		I _S	97	Α	
Pulsed drain current ^b		I _{DM}	280		
Single pulse avalanche current	L = 0.1 mH	I _{AS}	46		
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	105.8	mJ	
Maximum power dissipation ^b	T _C = 25 °C	P _D	107	W	
	T _C = 125 °C		35	VV	
Operating junction and storage temperature	range	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	R_{thJA}	50	°C/W
Junction-to-case (drain)		R_{thJC}	1.4	C/VV

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•		I.		I.	L
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		40	-	-	V
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	2.5	3.0	3.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 40 V, T _J = 125 °C	-	-	50	μA
		V _{GS} = 0 V	V _{DS} = 40 V, T _J = 175 °C	-	-	500	μΑ
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	50	-	-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.00190	0.00233	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.00390	Ω
		V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.00470	
Forward transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	84	-	S
Dynamic ^b							
Input capacitance	C _{iss}			-	5405	8000	
Output capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 25 V, f = 1 MHz	-	1942	2700	pF
Reverse transfer capacitance	C _{rss}				175	250	-
Total gate charge ^c	Qg			-	84	130	
Gate-source charge c	Q _{gs}	$V_{GS} = 10 \text{ V}$ $V_{DS} = 20 \text{ V}, I_D = 50 \text{ A}$		-	29.5	-	nC
Gate-drain charge c	Q _{gd}				19.5	-	
Gate resistance	R _g	f = 1 MHz		1	2	3	Ω
Turn-on delay time ^c	t _{d(on)}				17	30	
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 0.4 \Omega$ $I_{D} \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	17	30	
Turn-off delay time ^c	t _{d(off)}			-	34	60	ns
Fall time ^c	t _f			-	18	35	
Source-Drain Diode Ratings and Chara	cteristics ^b						
Pulsed current ^a	I _{SM}			-	-	280	Α
Forward voltage	V _{SD}	I _F = 25 A, V _{GS} = 0 V		-	0.8	1.5	V
Body diode reverse recovery time	t _{rr}	I _F = 50 A, di/dt = 100 A/μs		-	41	85	ns
Body diode reverse recovery charge	Q _{rr}			-	28	60	nC
Reverse recovery fall time	ta			-	24	-	
Reverse recovery rise time	t _b			-	17	-	ns
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.36	-	Α

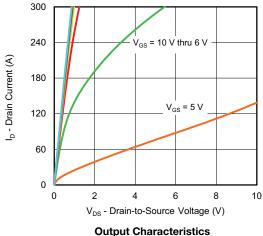
Notes

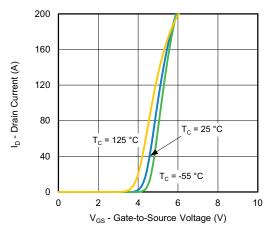
- a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

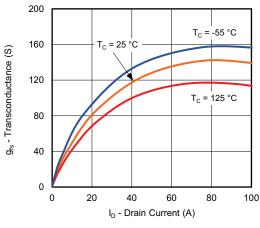


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

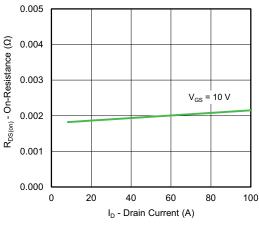




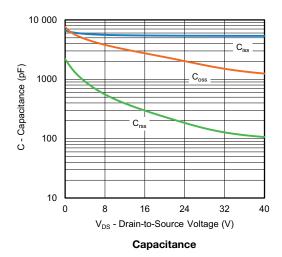
Transfer Characteristics

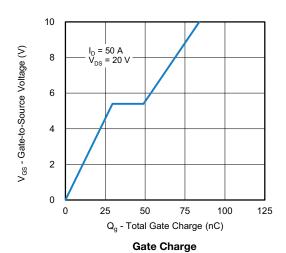


Transconductance



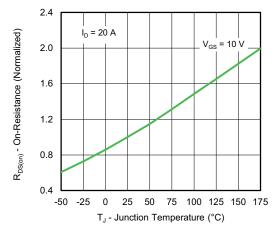
On-Resistance vs. Drain Current



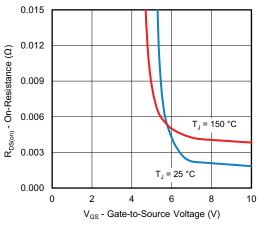




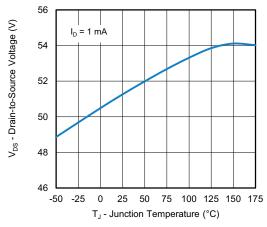
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



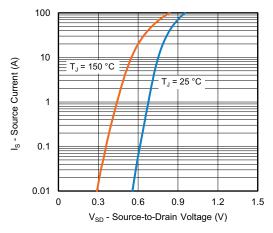
On-Resistance vs. Junction Temperature



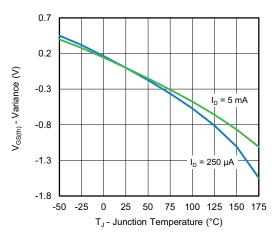
On-Resistance vs. Gate-to-Source Voltage



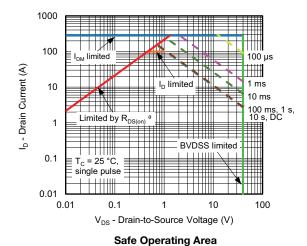
Drain Source Breakdown vs. Junction Temperature



Source Drain Diode Forward Voltage



Threshold Voltage



Care Op

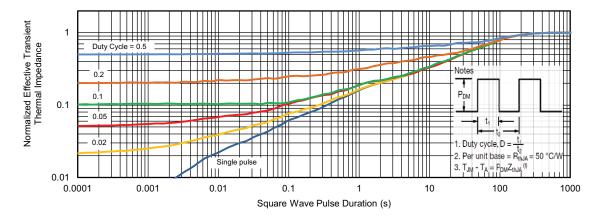
Note

a. V_{GS} > minimum V_{GS} at which R_{DS(on)} is specified

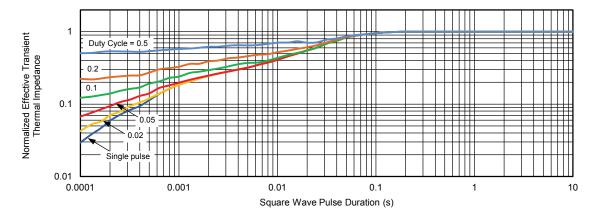
For technical questions, contact: automostechsu



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

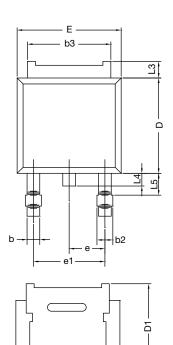
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

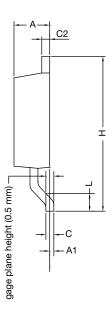
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?76909.



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TO-252AA Case Outline





	MILLIN	IETERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

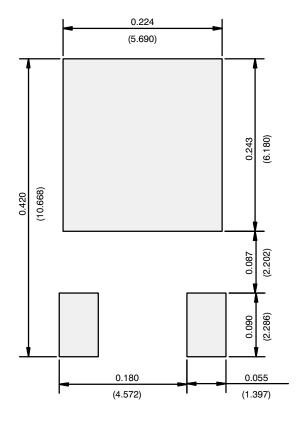
DWG: 6019

Note

• Dimension L3 is for reference only.



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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ATTLICATION NOT



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